

Designed for Ultra Broadband High Power applications, this amplifier utilizes linear Silicon RF Power MOSFET devices that provide high gain, wide dynamic range and good linearity. Exceptional performance, long term reliability and high efficiency are achieved by employing advanced broadband RF matching networks and combining techniques, EMI/RFI filters, custom-machined housings and qualified components. Each unit undergoes extensive burn-in prior to final test and inspection.

ELECTRICAL SPECIFICATIONS

Characteristics	Rating	Limit
Frequency Response	1 – 1000 MHz	Min
Power Output CW	25 Watts	Min
Power Output @ 1 dB comp.	12 Watts	Min
Third Order Intercept Point	+50 dBm	Typ
Small Signal Gain	46 dB	Min
Small Signal Gain Flatness	±1.5 dB	Max
Input Overdrive	+10 dBm	Max
Input/Output VSWR @ 50 ohm	2:1	Max
Harmonics @ 1 dB compression	-20 dBc	Typ
Noise Figure	10 dB	Max
Spurious Signals	-60 dBc	Max
Supply Voltage (single phase)	100 - 240 VAC	Nom
Power Consumption	150 Watts AC	Max

MECHANICAL SPECIFICATIONS

Dimensions (Bench Top)	8.5"x3.5"x16"	Max
Weight	20 lb.	Max
RF Connectors	Type-N front panel	
Cooling:	Internal forced-air	

ENVIRONMENTAL CHARACTERISTICS

Operating Temperature: 0°C to +50°C

Non-operating Temperature: -40°C to +85°C

Humidity: 95% relative without condensation

Altitude: 10,000 feet

Shock and Vibration: Normal truck transport

CIRCUIT PROTECTIONS

Infinite Load VSWR

RF Input Overdrive

Thermal Overload

AVAILABLE OPTIONS

- Front or Rear Panel Connectors
- Rack mount Chassis
- LCD Digital Display
 - Forward and Reverse Reading
 - Gain Adjustment
 - Automatic Level Control
 - Standby Mode
 - Fault Indication
- IEEE-488 GPIB or RS-232 Interface